

TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

1SS383

Low Voltage High Speed Switching

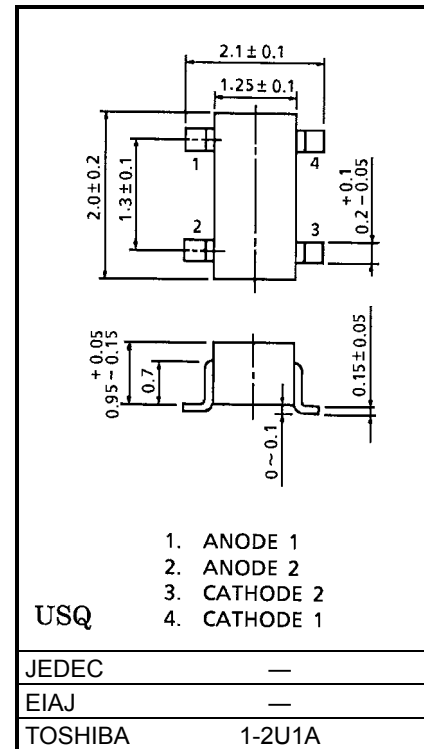
Unit: mm

- Small package
- Composed of 2 independent diodes.
- Low forward voltage: $V_F (3) = 0.54V$ (typ.)
- Low reverse current: $I_R = 5\mu A$ (max)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	V_{RM}	45	V
Reverse voltage	V_R	40	V
Maximum (peak) forward current	I_{FM}	300 *	mA
Average forward current	I_O	100 *	mA
Surge current (10ms)	I_{FSM}	1 *	A
Power dissipation	P	100 *	mW
Junction temperature	T_j	125	$^\circ C$
Storage temperature range	T_{stg}	-55~125	$^\circ C$
Operating temperature range	T_{opr}	-40~100	$^\circ C$

*: Unit rating. Total rating = unit rating $\times$ 1.5

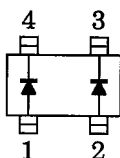


Weight: 0.006g

Electrical Characteristics ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F (1)$	—	$I_F = 1mA$	—	0.28	—	V
	$V_F (2)$	—	$I_F = 10mA$	—	0.36	—	V
	$V_F (3)$	—	$I_F = 100mA$	—	0.54	0.60	V
Reverse current	I_R	—	$V_R = 40V$	—	—	5	μA
Total capacitance	C_T	—	$V_R = 0, f = 1MHz$	—	18	25	pF

Pin Assignment (Top View)



Marking

